BPM Microsystems improves flash memory programmer

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To keep pace with the changing aspects of flash memory technology, BPM Microsystems has introduced a number of improvements to its Flashstream vector programming system. By the end of 2008, Flashstream will support memories up to 32 Gbits and will be hardware-upgradeable as higher-density devices become available in the marketplace. It also accommodates cache-programming modes in select devices, pushing the top speed of data transfer during programming on NAND memory to 8.23 Mbytes/s.

The programmer now works with Multi-Level Cell (MLC) flash memory using a proprietary bit-error-rate tolerance method to handle the unique requirements of this NAND technology without additional overhead. Managed NAND devices, including Samsung's MoviNAND, Micron's e-MMC, and Sandisk's iNAND, are also now supported. According to the manufacturer, Flashstream is the only mass programming system on the market for the Samsung MoviNAND family of devices.

Enhancements to Flashstream's vector engine maximizes performance with address-data-multiplexed NOR devices, which are increasingly gaining design wins in mobile phones and other portable devices. Bad block management options in the BPWin software have been enhanced so that more than 90 percent of standard bad block management schemes can be addressed without the need for customization by BPM. Bad block parameters can be permanently recorded to the master programming file and transferred to manufacturing facilities worldwide with the same success that was achieved during original setup. The standard bad block tool set is included with the purchase of the Flashstream programmer.

Flashstream manual and automated programmers support more than 800 NAND, NOR, and EEPROM devices from 12 different manufacturers. The company can support a new device on any of its programming systems in one week once samples and specifications are provided.